

Figures for abstract

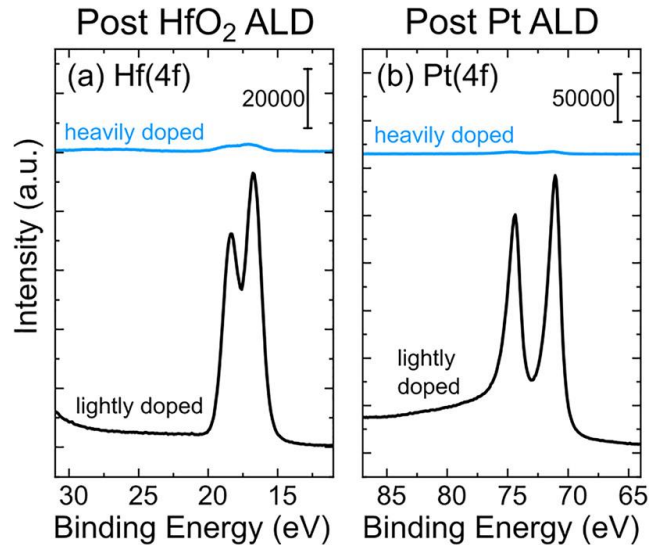


Figure 1. (a) Hf(4f) XPS spectra after HfO₂ ALD showing selective deposition on lightly doped region and little deposition on heavily doped region. (b) Pt(4f) XPS spectra after Pt ALD (immediately following HfO₂ ALD) showing selective deposition on HfO₂ in lightly doped region and little deposition on heavily doped region. [1]

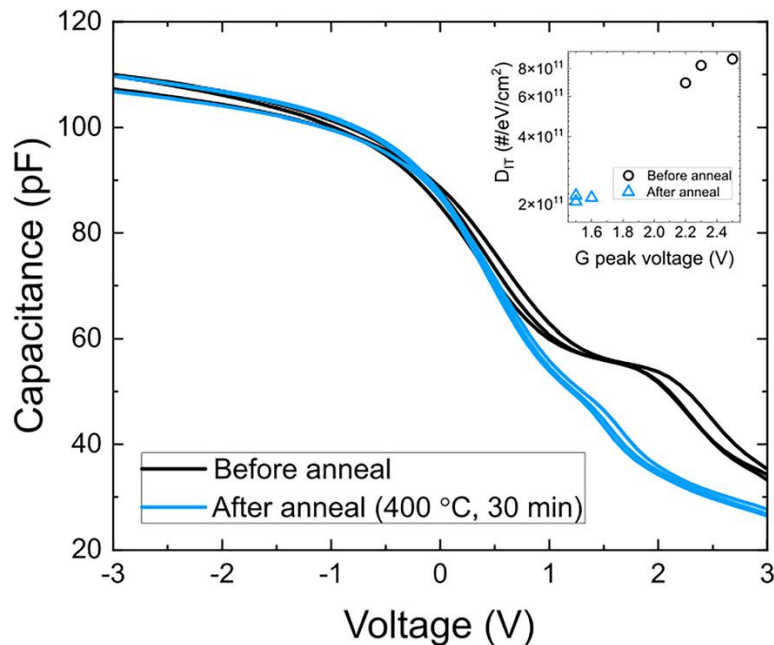


Figure 2. Capacitance v. voltage behavior of three selectively-deposited Pt-HfO₂-Si capacitors before and after a forming gas anneal. Inset shows estimated interface state densities before and after forming gas anneal. [1]

[1] Brummer, Amy C., et al. "Fabrication and characterization of a self-aligned gate stack for electronics applications." *Applied Physics Letters* 119.14 (2021): 142901.